



## Few-Layer Transition Metal Dichalcogenide Exfoliation, Characterization, and Modeling for Future Electronics

Matei Jordache, Jierui Liang, Susan Fullerton

Department of Chemical and Petroleum Engineering, University of Pittsburgh



mcj21@pitt.edu

### Goal

- Exfoliate monolayer flakes of transition metal dichalcogenides (TMDs) for characterization and devices, simulation of electrical and mechanical device behavior

### Motivation

- Thin TMD flakes exhibit unique electrical properties (high mobility, small band gap<sup>[1]</sup>) and mechanical properties (high flexibility<sup>[2]</sup>)
- Attractive for construction of low-power, nanoscale devices and memory, leading to demand for reliable source of flakes for prototyping

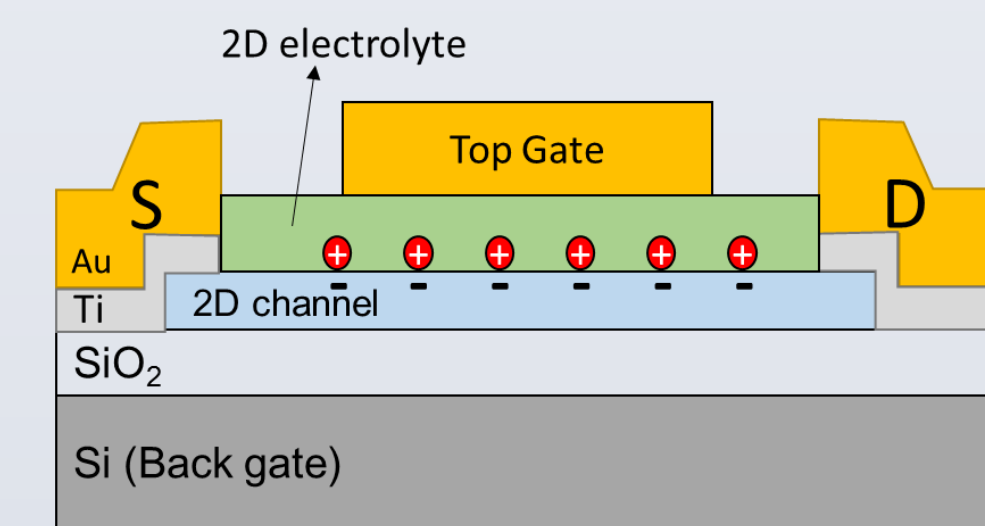


Fig. 1 Schematic of proposed device, using exfoliated MoS<sub>2</sub> and graphene as the 2D channel and top gate, respectively.

### Exfoliation

- Mechanical exfoliation of thin flakes using the standard method, Figure 2.

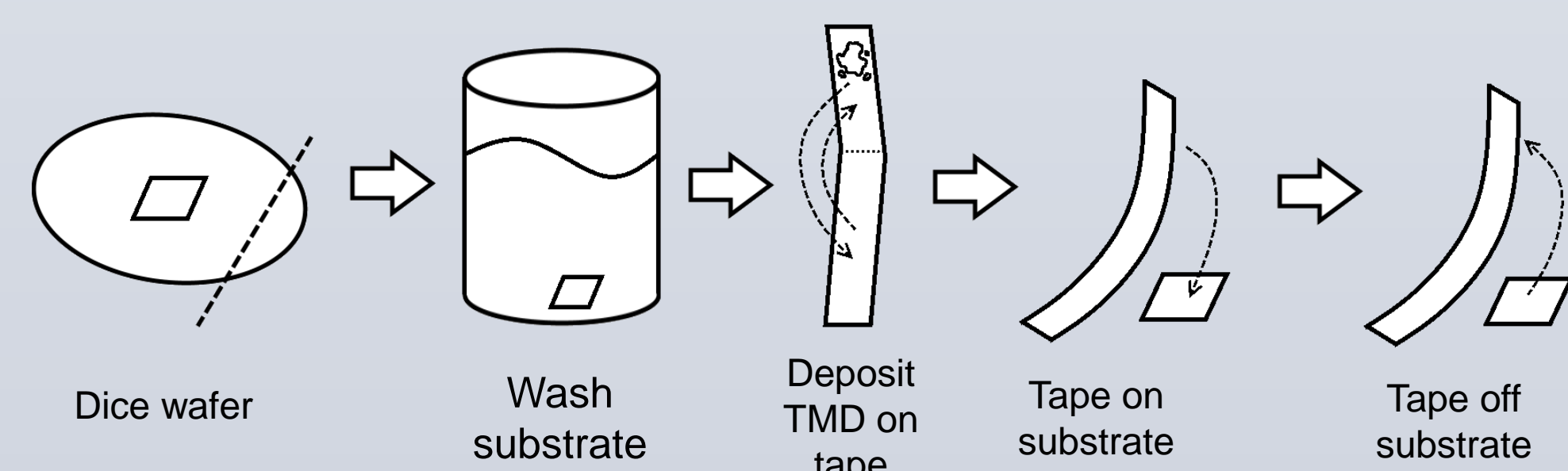


Fig. 2 Standard method for exfoliating thin flakes.

- A candidate flake for a device is longer than 15µm and thinner than 10nm.
- Standard method for MoS<sub>2</sub> yields poor results (2-3µm lateral size, 10-15nm thick)
- Experimenting with modifications to exfoliation process:
  - Thermal Annealing<sup>[3]</sup>
    - Anneal substrate for 5 minutes at 100° C prior to exfoliation
  - Reactive Ion Etching (RIE)<sup>[3]</sup>
    - Clean substrate with O<sub>2</sub> plasma prior to exfoliation
  - Varying levels of adhesive to perform exfoliation
    - Low (name), medium (name), high (Scotch)

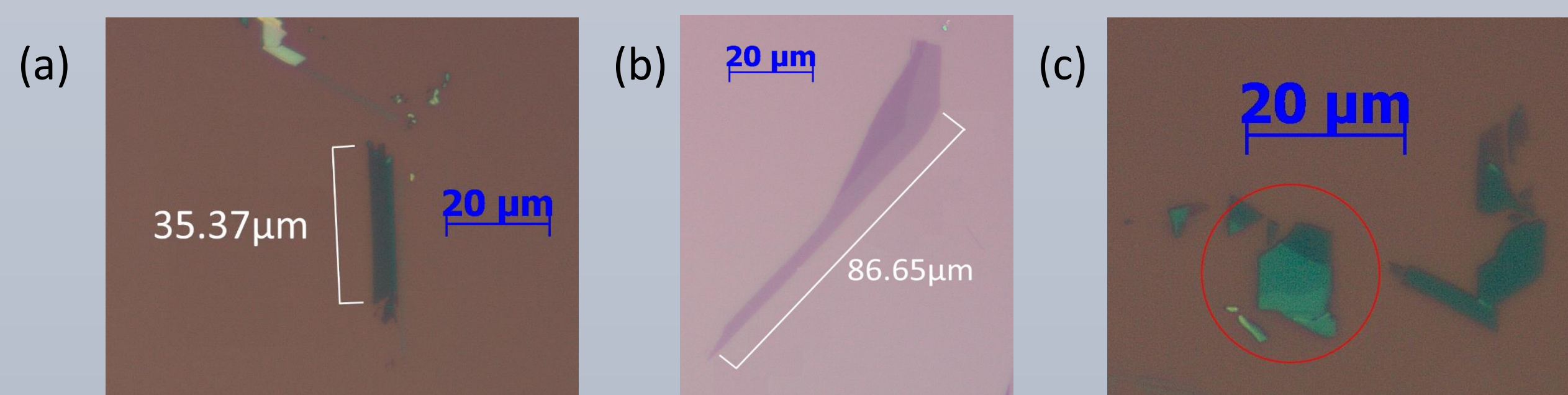


Fig. 3 Optical images of few-layer flakes. (a) Candidate MoS<sub>2</sub> flake exfoliated using thermal annealing. (b) Candidate graphene flake exfoliated using standard method. (c) An unusable flake (too thick).

### Alternate MoS<sub>2</sub> Exfoliation Method Results

- Annealing with the medium adhesive tape (Fig. 4b) and annealing + RIE with low adhesive tape (Fig 4a) gave the best results with 1/2 depositions

- RIE is an expensive and time-consuming process
- Annealing with 1/2 depositions using medium tape best option

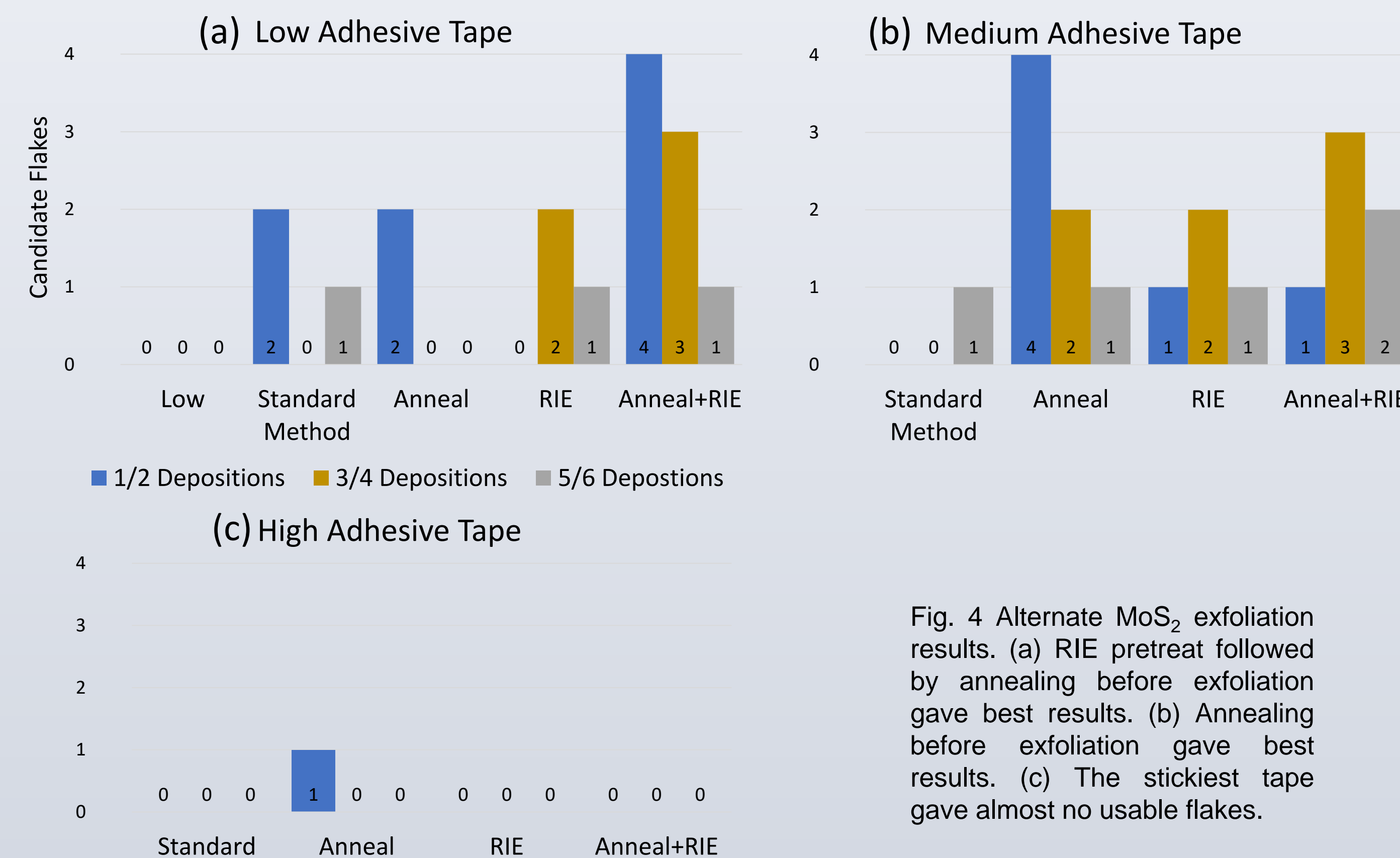


Fig. 4 Alternate MoS<sub>2</sub> exfoliation results. (a) RIE pretreat followed by annealing before exfoliation gave best results. (b) Annealing before exfoliation gave best results. (c) The stickiest tape gave almost no usable flakes.

### Modeling

- When few-layer TMDs are bent, they undergo a phase transition from semiconductor to metal<sup>[4]</sup>
  - This phase transition happens at 3% strain in MoTe<sub>2</sub>
  - This can be reached at 3V with a channel length of 2.5µm.
- To bend the flake, use an ionic polymer metal composite (IPMC)
  - In an IPMC, the anions are held in place, but the cations are free to move under bias. This causes a mechanical deformation of the material due to electrostatic pressure<sup>[5]</sup>
  - The strain  $\epsilon$  on the plane can be found using the following equations<sup>[6]</sup>, where  $\alpha$  is the magnitude of steric strain,  $\beta$  is the electrostatic pressure, and  $\gamma$  is the crowding factor.

$$\epsilon = \frac{S-L}{L}, \quad S = \frac{\theta}{K}, \quad \theta = \cos^{-1}\left(\frac{2R^2-L^2}{2R^2}\right),$$

$$K(V) = \alpha\sqrt{1-\gamma} \frac{V}{\sqrt{1+\frac{V}{8}}} + \frac{2}{3}\beta(1-2\gamma)\sqrt{2(1-\gamma)}V^{\frac{3}{2}}$$

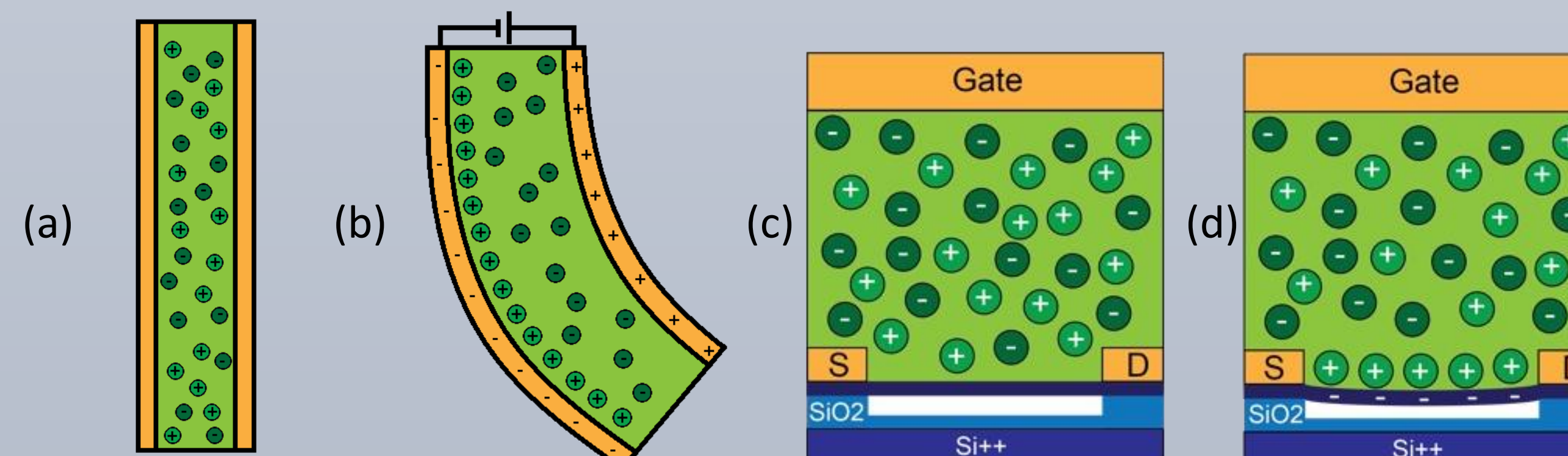


Fig. 5: Proposed mechanics of strain-based device. (a) Schematic of IPMC device with no bias between the contacts. (b) Schematic of the IPMC device with voltage applied. (c) Device with no bias. (d) Device with V<sub>G</sub> > 0, causing strain on MoTe<sub>2</sub>

### Characterization

- Using AFM to quantify:
  - Lateral size: small flakes (<10µm) cannot be used in devices
  - Thickness: New exfoliation methods lead to flake thickness approaching monolayer MoS<sub>2</sub> (0.3nm)
  - Roughness: If surface too rough (R<sub>Q</sub> < 1.5nm) monolayer electrolyte (CoCRPC) will not lay flat

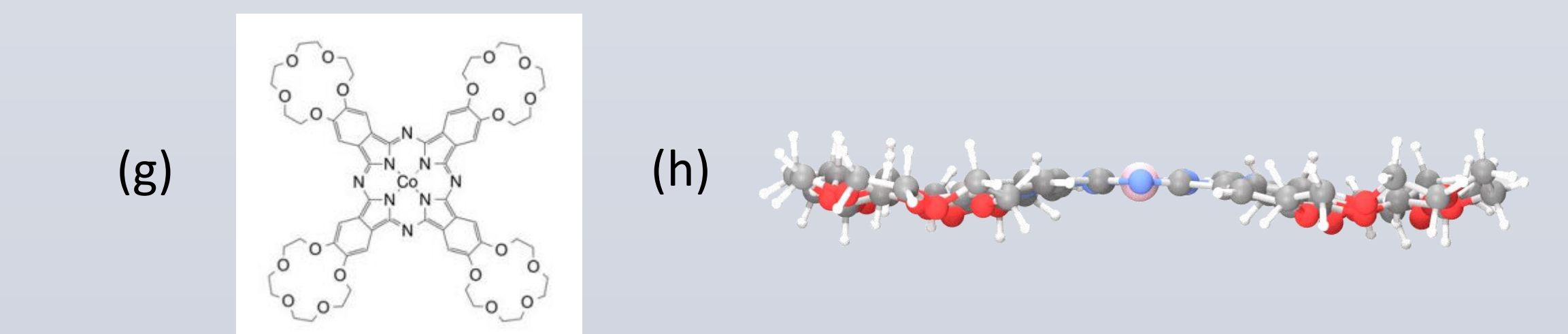
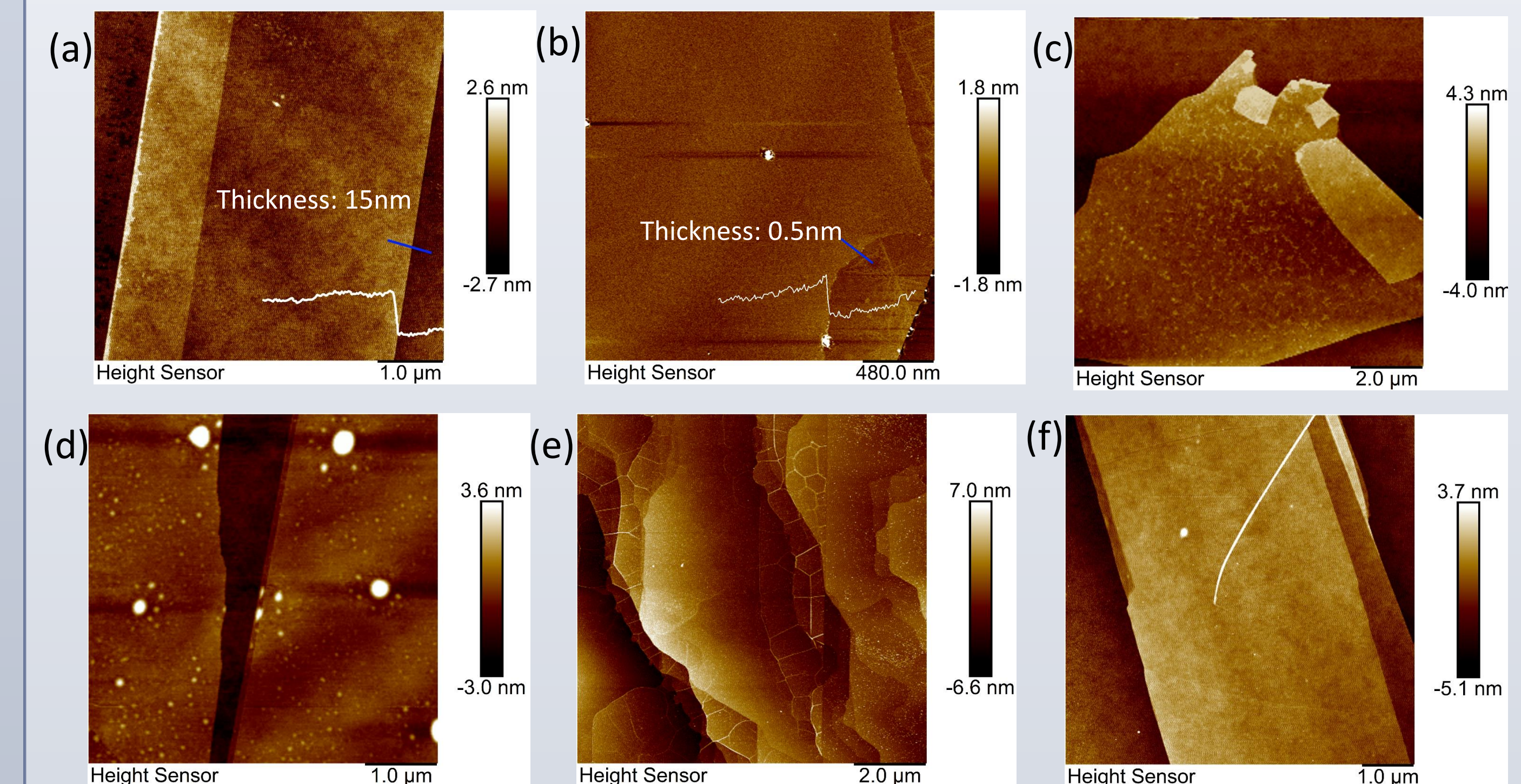


Fig. 4 AFM images of few-layer flakes. (a) Step edge of uncoated MoS<sub>2</sub> flake. (b) Step edge on homogeneous CoCrPC monolayer on exfoliated graphene. (c) Bare boron nitride (BN) flake, used as an insulator. (d) A close-up of a crack in a MoS<sub>2</sub> flake. (e) Epitaxially grown graphene after photoresist removal. (f) Wrinkled MoS<sub>2</sub> flake. (g) Monolayer electrolyte cobalt crown ether phthalocyanine (CoCRPC) top view. (h) Monolayer electrolyte (CoCRPC) side view with Li<sup>+</sup> ions solvated in crown ethers.

### Conclusions and Future Work

- Adding the thermal annealing step during exfoliation allows for more consistent flake thickness and lateral size in MoS<sub>2</sub>
- The difference in exfoliation results between graphene and MoS<sub>2</sub> suggests that each material may need a different process or substrate.
- Annealing does not leave any residue from the tape on the flakes.

#### Future work:

- Explore other TMD materials such as tungsten diselenide (WSe<sub>2</sub>), and exfoliation methods
- Use C-AFM for measuring electrical properties of flakes/coatings
- Use COMSOL to determine electrical and mechanical properties of devices that undergo strain

#### References

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